



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 60 Volts CURRENT 0.250 Ampere

CHT870PT

Lead free devices

APPLICATION

- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

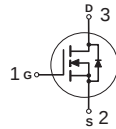
FEATURE

- * Small surface mounting type. (SC-59)
- * High density cell design for low $R_{DS(ON)}$.
- * Suitable for high packing density.
- * Rugged and reliable.
- * High saturation current capability.
- * Voltage controlled small signal switch.

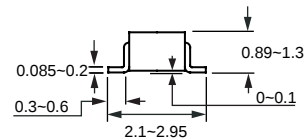
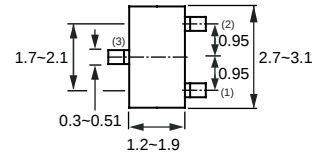
CONSTRUCTION

- * N-Channel Enhancement

CIRCUIT



SC-59/SOT-346



Dimensions in millimeters

SC-59/SOT-346

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	CHT870PT	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} \leq 1 \text{ M}\Omega$)	60	V
V_{GSS}	Gate-Source Voltage - Continuous	± 20	V
	- Non Repetitive ($t_p < 50 \mu\text{s}$)	± 40	
I_D	Maximum Drain Current - Continuous	250	mA
	- Pulsed	190	
P_D	Maximum Power Dissipation	320	mW
		210	mW
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300	$^\circ\text{C}$

Thermal characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	400	$^\circ\text{C/W}$
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2002-7

RATING CHARACTERISTIC CURVES (CHT870PT)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 100\mu\text{A}$	60	80		V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$T_C = 125^\circ\text{C}$			0.5	mA
I_{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$			10	nA
I_{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -15\text{ V}, V_{DS} = 0\text{ V}$			-10	nA

ON CHARACTERISTICS (Note 1)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	2.0	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 250\text{ mA}$		2.0	5.0	Ω
		$V_{GS} = 4.0\text{ V}, I_D = 100\text{ mA}$		2.5	4.0	
$V_{DS(on)}$	Drain-Source On-Voltage	$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$		0.6	3.75	V
		$V_{GS} = 5.0\text{ V}, I_D = 50\text{ mA}$		0.09	1.5	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 7.5V_{DS(on)}$	800	1800		mA
		$V_{GS} = 4.5\text{ V}, V_{DS} = 10V_{DS(on)}$	500	700		
g_{FS}	Forward Transconductance	$V_{DS} = 15\text{ V}_{DS(on)}, I_D = 200\text{ mA}$	100			mS

DYNAMIC CHARACTERISTICS

Q_g	Total Gate Charge	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 250\text{ mA}$		0.6	1.0	nC
Q_{gs}	Gate-Source Charge			0.06	25	
Q_{gd}	Gate-Drain Charge			0.06	5	
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		25	50	pF
C_{oss}	Output Capacitance			6	25	
C_{rss}	Reverse Transfer Capacitance			1.2	5	
t_{on}	Turn-On Time	$V_{DD} = 30\text{ V}, R_L = 200\Omega,$ $I_D = 100\text{ mA}, V_{GS} = 10\text{ V},$ $R_{GEN} = 10\Omega$		7.5	20	nS
t_r				6		
t_{off}	Turn-Off Time	$V_{DD} = 30\text{ V}, R_L = 200\Omega,$ $I_D = 100\text{ mA}, V_{GS} = 10\text{ V},$ $R_{GEN} = 10\Omega$		7.5	20	nS
t_f				3		

Note:

1. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

RATING CHARACTERISTIC CURVES (CHT870PT)

Typical Electrical Characteristics

Figure 1. On-Region Characteristics

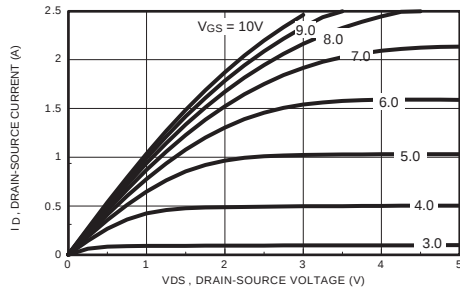


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

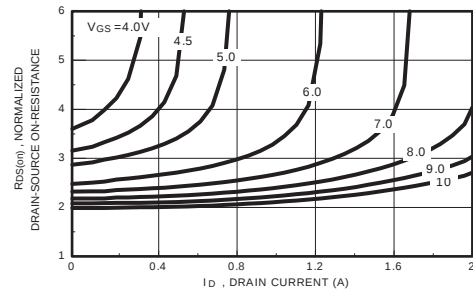


Figure 3. On-Resistance Variation with Temperature

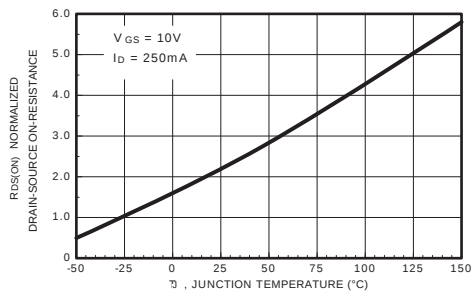


Figure 4. On-Resistance Variation with Drain Current and Temperature

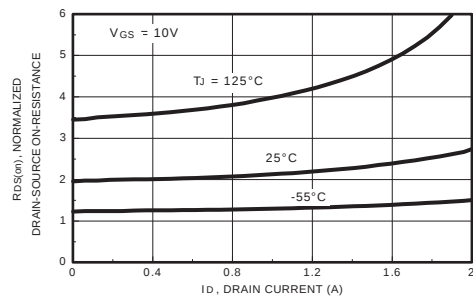


Figure 5. Transfer Characteristics

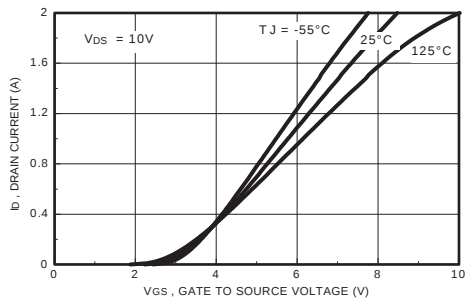
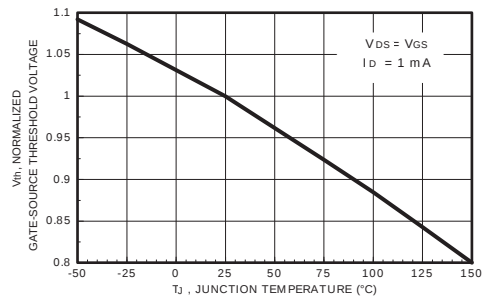


Figure 6. Gate Threshold Variation with Temperature



RATING CHARACTERISTIC CURVES (CHT870PT)

Typical Electrical Characteristics (continued)

Figure 7. Breakdown Voltage Variation with Temperature

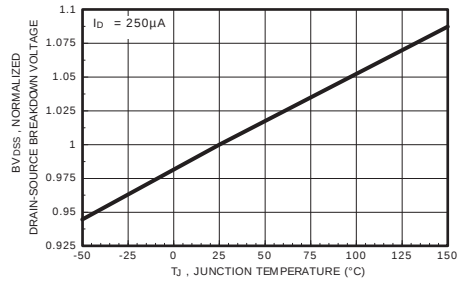


Figure 8. Body Diode Forward Voltage Variation with Drain Current

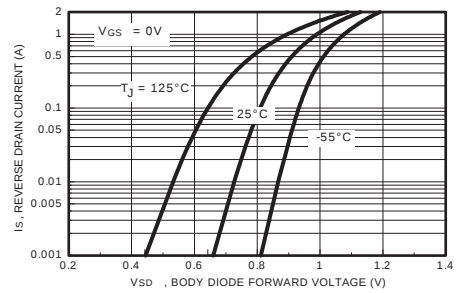


Figure 9. Capacitance Characteristics

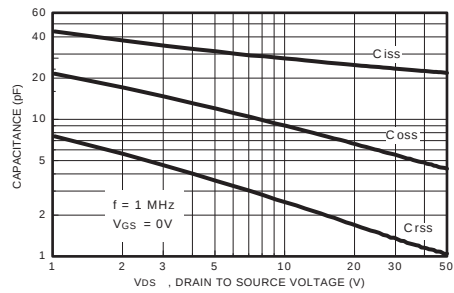


Figure 10. Gate Charge Characteristics

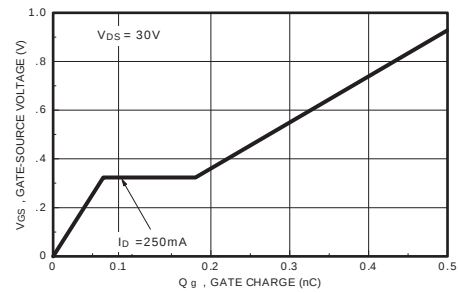


Figure 11.

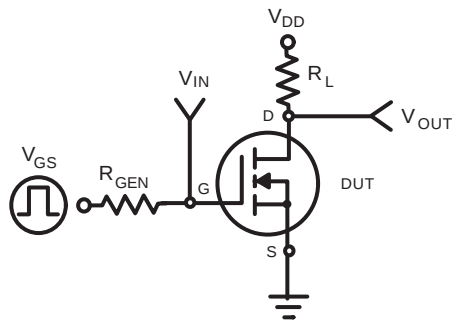


Figure 12. Switching Waveforms

